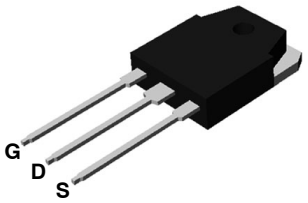
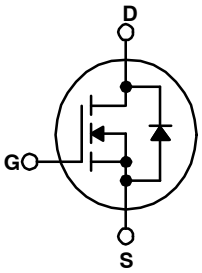
MOSFET – N-Channel UniFET™

250 V, 59 A, 49 mΩ

FDA59N25



TO−3P−3LD
CASE 340BZ



Description

UniFET MOSFET is **onsemi**'s high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on−state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.

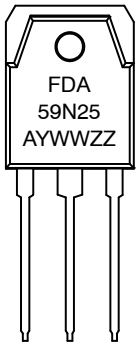
Features

- $R_{DS(on)}$ = 49 mΩ (Max.) @ V_{GS} = 10 V, I_D = 29.5 A
- Low Gate Charge (Typ. 63 nC)
- Low C_{rss} (Typ. 70 pF)
- 100% Avalanche Tested
- RoHS Compliant

Applications

- PDP TV
- Uninterruptible Power Supply
- AC−DC Power Supply

MARKING DIAGRAM



FDA59N25	= Specific Device Code
A	= Assembly Location
YWW	= Date Code (Year & Week)
ZZ	= Assembly Lot

ORDERING INFORMATION

Device	Package	Shipping†
FDA59N25	TO−3P−3LD (Pb−Free)	450 Units / Tube

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter		Rating	Unit
V_{DSS}	Drain to Source Voltage		250	V
$V_{DS(Avalanche)}$	Repetitive Avalanche Voltage (Notes 1, 2)		300	V
V_{GSS}	Gate to Source Voltage		±30	V
I_D	Drain Current	– Continuous (T_C = 25°C) – Continuous (T_C = 100°C)	59 35	A
I_{DM}	Drain Current	– Pulsed (Note 1)	236	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		1458	mJ
I_{AR}	Avalanche Current (Note 1)		59	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		39.2	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
P_D	Power Dissipation	(T_C = 25°C) – Derate Above 25°C	392 3.2	W W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		–55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8” from Case for 5 Seconds		300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse−width limited by maximum junction temperature.
2. L = 0.67 mH, I_{AS} = 59 A, V_{DD} = 50 V, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 59 A, di/dt ≤ 200 A/μs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.32	°C/W
$R_{\theta CS}$	Thermal Resistance, Case to Sink, Typ.	0.24	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain−Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	250	–	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	–	0.25	–	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 250 V, V_{GS} = 0 V	–	–	1	μA
		V_{DS} = 200 V, T_C = 125°C	–	–	10	μA
I_{GSSF}	Gate to Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	–	–	100	nA
I_{GSSR}	Gate to Body Leakage Current, Reverse	V_{GS} = −30 V, V_{DS} = 0 V	–	–	−100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	3.0	–	5.0	V
$R_{DS(on)}$	Static Drain−Source On−Resistance	V_{GS} = 10 V, I_D = 29.5 A	–	0.041	0.049	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40 V, I_D =29.5 A	–	45	–	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz	–	3090	4020	pF
C_{oss}	Output Capacitance		–	630	820	pF
C_{rss}	Reverse Transfer Capacitance		–	70	110	pF
Switching Characteristics						
$t_{d(on)}$	Turn−On Delay Time	V_{DD} = 125 V, I_D = 59 A, V_{GS} = 10 V, R_G = 25 Ω (Note 4)	–	70	150	ns
t_r	Turn−On Rise Time		–	480	970	ns
$t_{d(off)}$	Turn−Off Delay Time		–	90	190	ns
t_f	Turn−Off Fall Time		–	170	350	ns
Qg	Total Gate Charge	V_{DS} = 200 V, I_D = 59 A, V_{GS} = 10 V (Note 4)	–	63	82	nC
Qgs	Gate−Source Charge		–	18.5	–	nC
Qgd	Gate−Drain Charge		–	30	–	nC
Drain−Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain−Source Diode Forward Current		–	–	59	A
I_{SM}	Maximum Pulsed Drain−Source Diode Forward Current		–	–	236	A
V_{SD}	Drain−Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 59 A	–	–	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 59 A, dI_F/dt = 100 A/μs	–	190	–	ns
Q_{rr}	Reverse Recovery Charge		–	4.4	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL PERFORMANCE CHARACTERISTICS

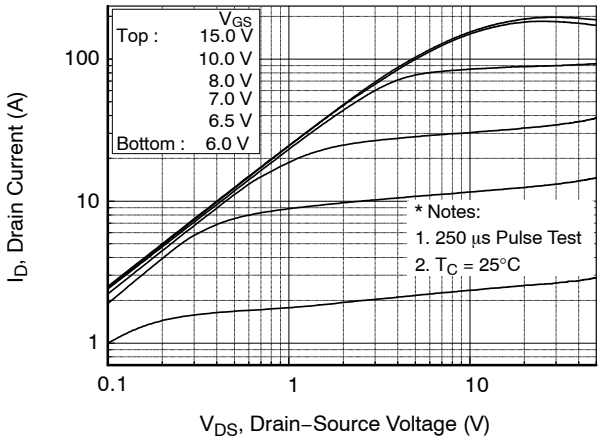


Figure 1. On−Region Characteristics

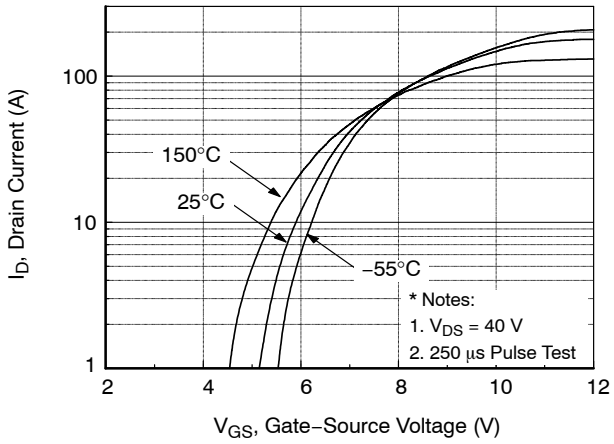


Figure 2. Transfer Characteristics

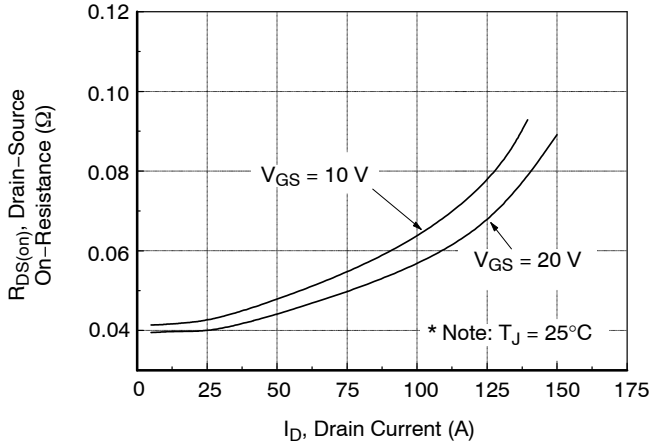


Figure 3. On−Resistance Variation vs. Drain Current and Gate Voltage

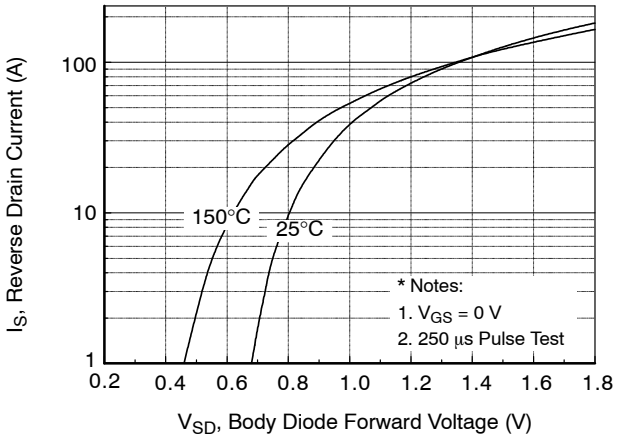


Figure 4. Body Diode Forward Voltage Variation vs. Source Current And Temperature

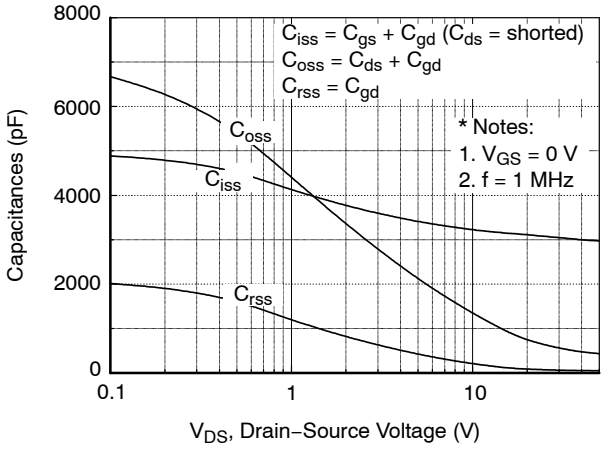


Figure 5. Capacitance Characteristics

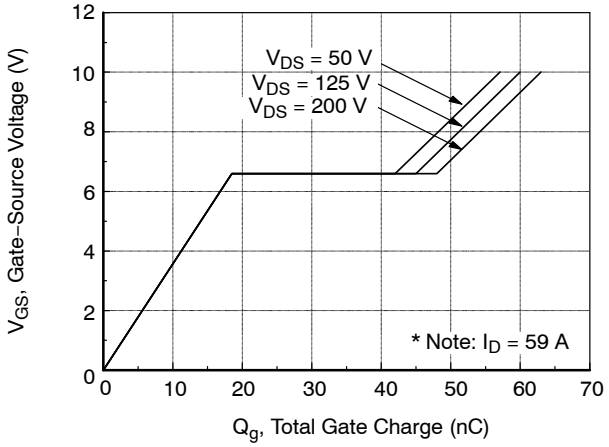


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

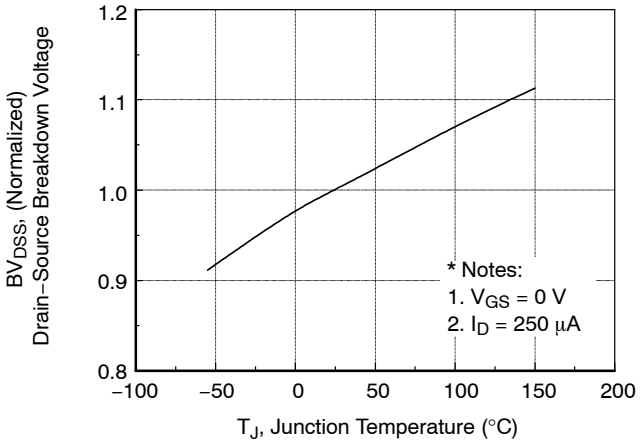


Figure 7. Breakdown Voltage Variation vs. Temperature

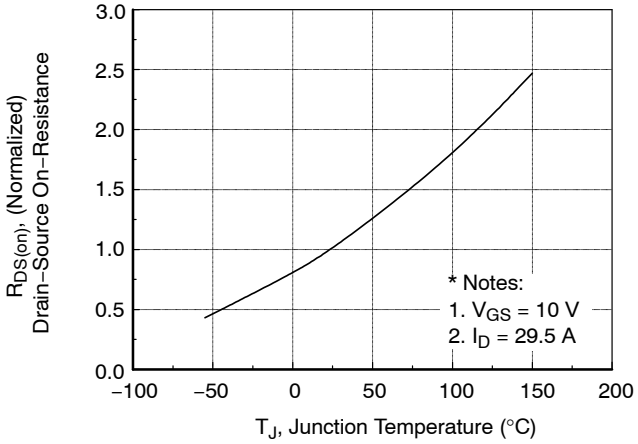


Figure 8. On−Resistance Variation vs. Temperature

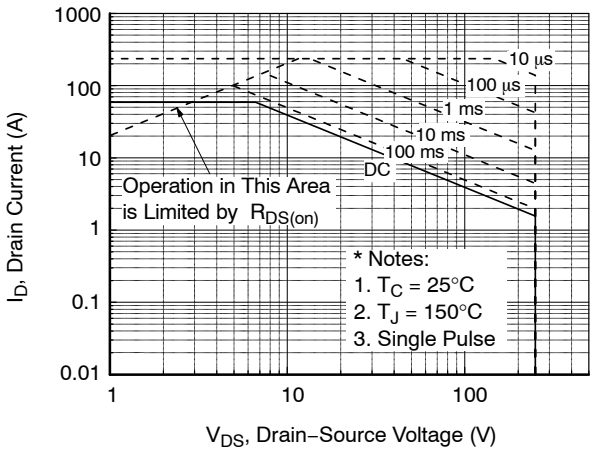


Figure 9. Maximum Safe Operating Area

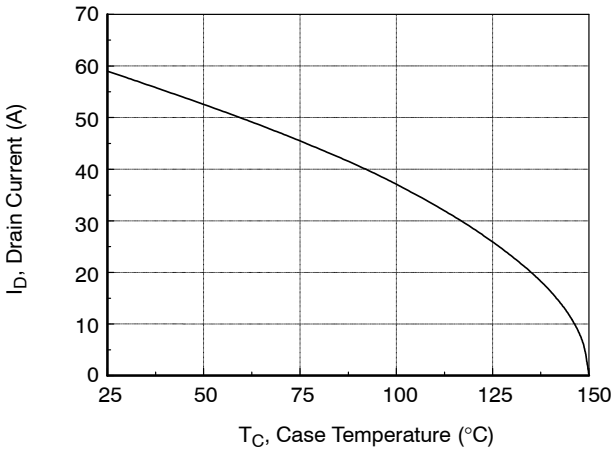


Figure 10. Maximum Drain Current vs. Case Temperature

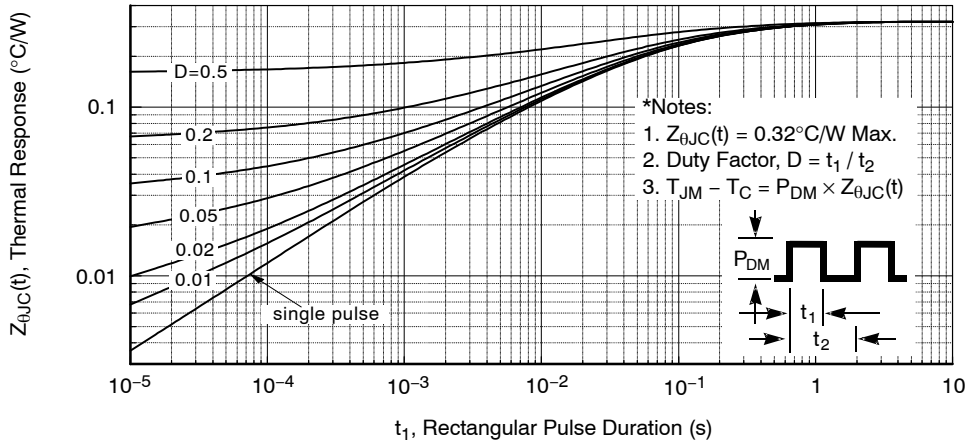


Figure 11. Transient Thermal Response Curve

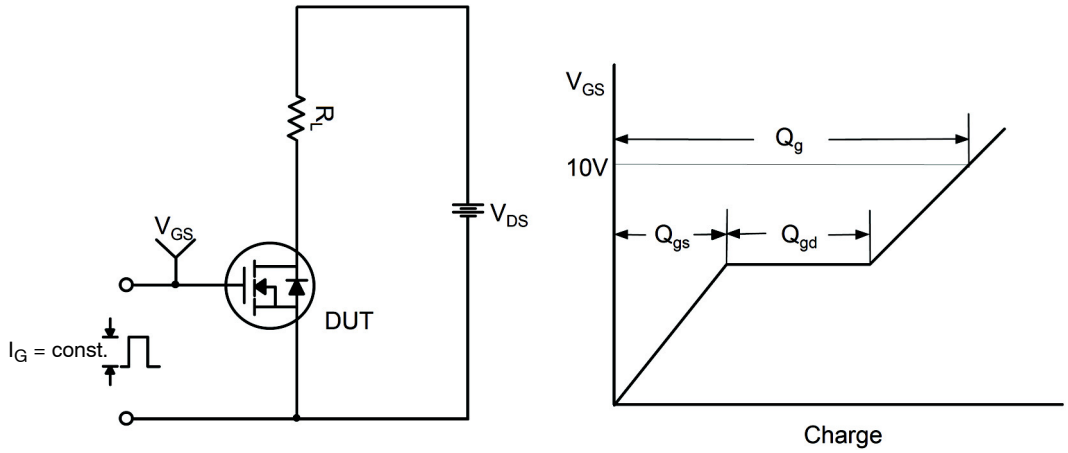


Figure 12. Gate Charge Test Circuit & Waveform

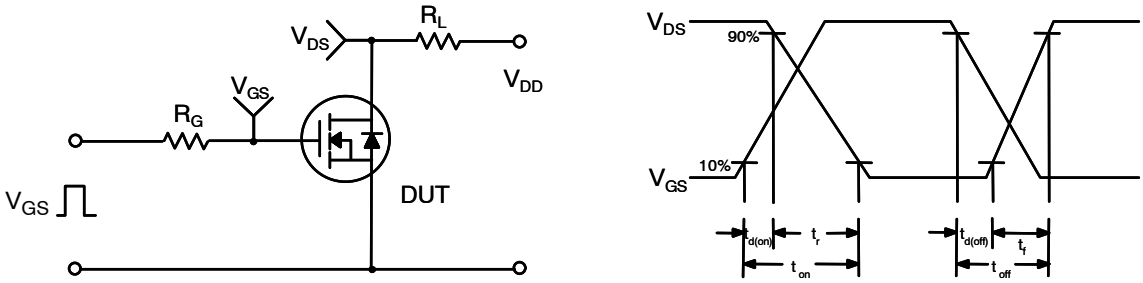


Figure 13. Resistive Switching Test Circuit & Waveforms

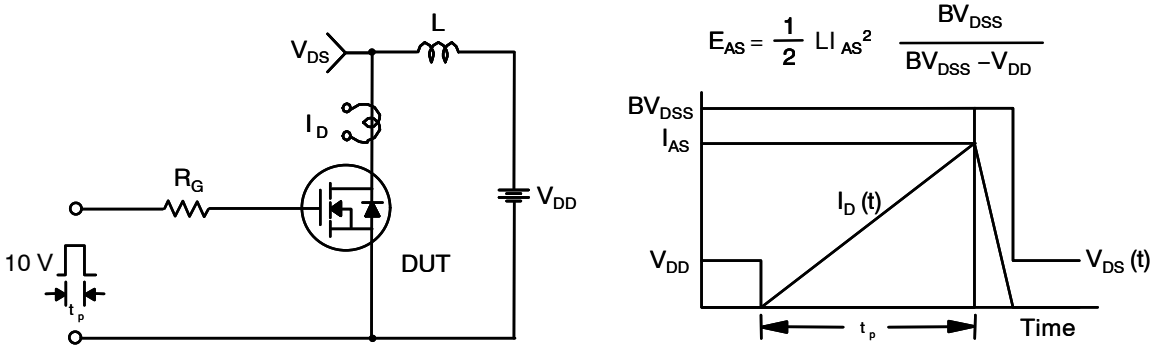


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

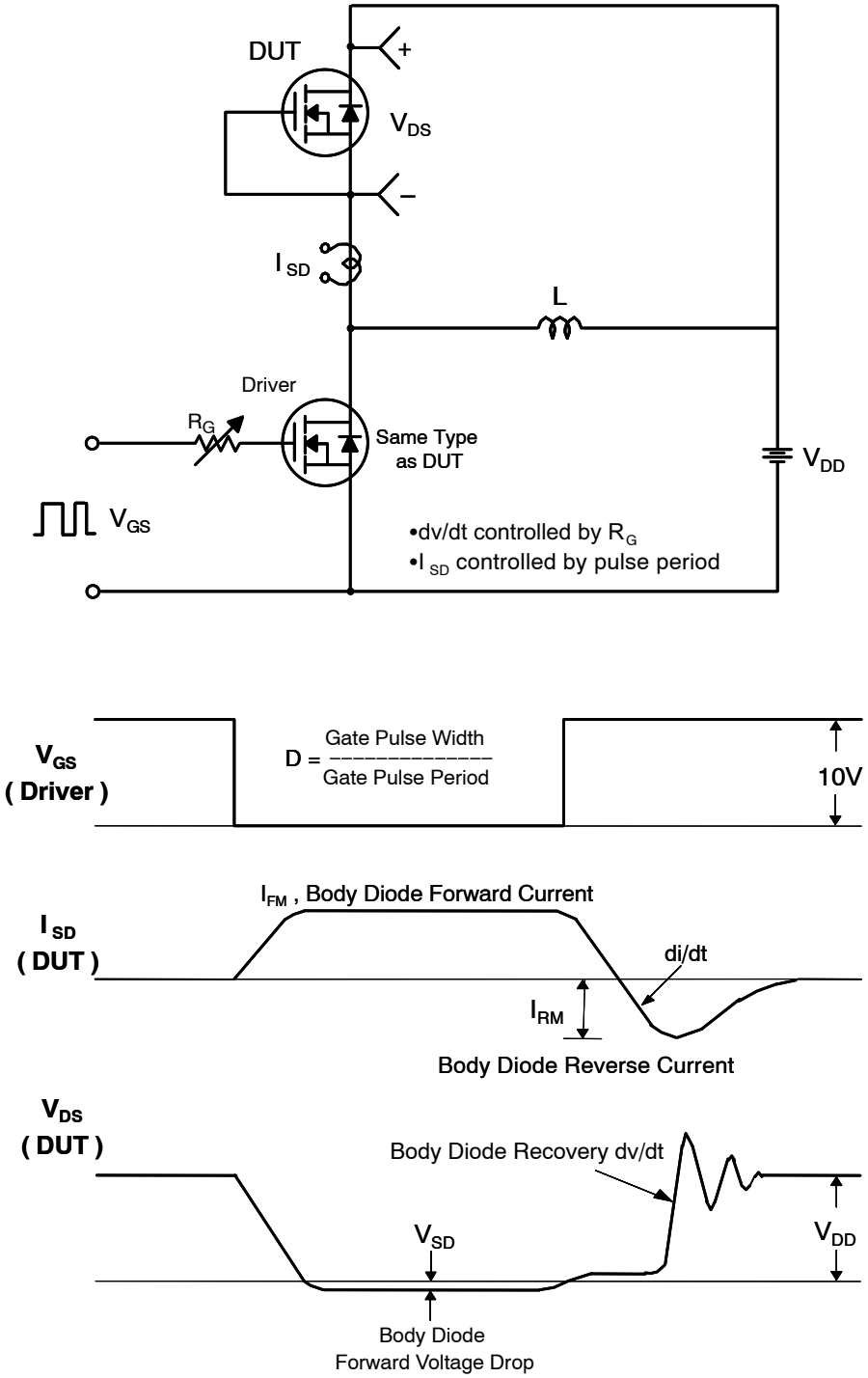


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

TO−3P−3LD / EIAJ SC−65, ISOLATED
CASE 340BZ
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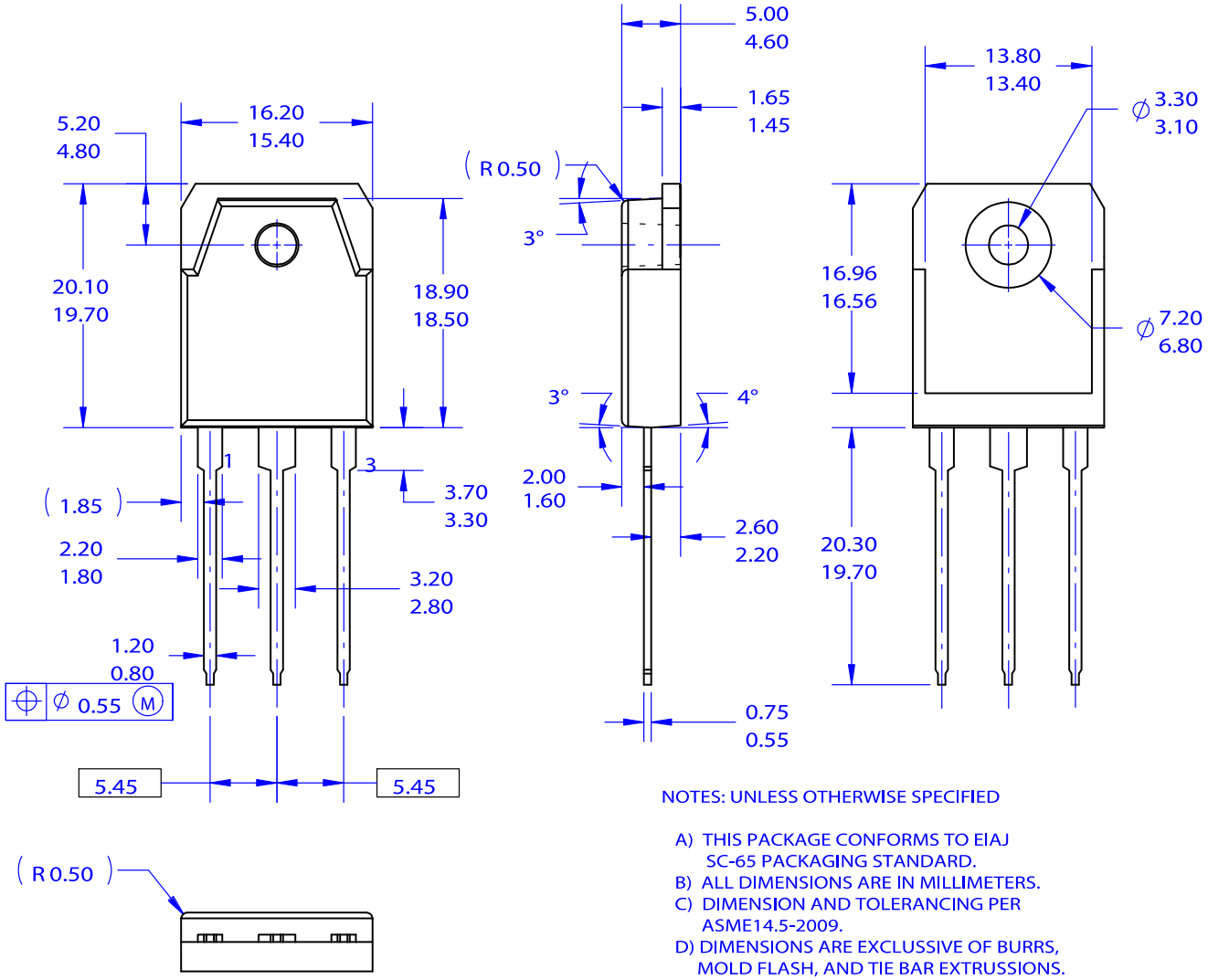
DATE 31 OCT 2016



NOTES: UNLESS OTHERWISE SPECIFIED

A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSION AND TOLERANCING PER ASME14.5-2009.
D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.

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